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Dual passivation of GaAs (110) surfaces using O$_2$/H$_2$O and trimethylaluminum

Tyler J. Kent,$^1$ Mary Edmonds,$^1$ Evgenii Chagarov,$^2$ Ravi Droopad,$^3$
and Andrew C. Kummel$^{1,2,a)$

$^1$Materials Science and Engineering Program, University of California, San Diego, La Jolla, California 92093, USA
$^2$Department of Chemistry and Biochemistry, University of California, San Diego, La Jolla, California 92093, USA
$^3$Department of Physics, Texas State University, San Marcos, Texas 78666, USA

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The nucleation and passivation of oxide deposition was studied on defect-free GaAs (110) surfaces to understand passivation of surfaces containing only III-V heterobonds. The passivation process on GaAs (110) was studied at the atomic level using scanning tunneling microscopy while the electronic structure was determined by scanning tunneling spectroscopy (STS). The bonding of the oxidant and reductant were modeled with density functional theory. To avoid Fermi level pinning during gate oxide atomic layer deposition, a dual passivation procedure was required using both a reductant, trimethylaluminum (TMA), and an oxidant, O$_2$ or H$_2$O. Dosing GaAs (110) with TMA resulted in the formation of an ordered complete monolayer of dimethylaluminum which passivates the group V dangling bonds but also forms metal-metal bonds with conduction band edge states. These edge states were suppressed by dosing the surface with oxidants O$_2$ or H$_2$O which selectively react with group III-aluminum bonds. The presence of an ordered Al monolayer with a high nucleation density was indirectly confirmed by XPS and STS. © 2013 AIP Publishing LLC. [http://dx.doi.org/10.1063/1.4852155]

I. INTRODUCTION

Silicon based metal oxide semiconductor field effect transistors (MOSFETs) may soon reach their physical performance limits.$^1$ As a consequence, many alternative semiconductors are being explored for use as channel materials. III-V semiconductors are attractive channel materials due to their high electron mobilities. A limiting factor in III-V based MOSFET performance is the high-k gate oxide/III-V interface because it usually has a large density of interfacial trap states (Dit).$^2$ Several theories have been proposed to explain the origin of interfacial trap states.$^3$ Studies have suggested these states are caused by native defects such as dangling bonds on the semiconductor surface, strained bonds on semiconductor surface atoms, and metal-metal bonds at the interface.$^4$ The majority of III-V based MOSFETs are fabricated using the group V rich (001)-(2×4) surface because this is the most easily obtained surface reconstruction.$^5$ This surface usually contains at least 42% defect unit cells which prevent efficient Fermi level modulation.$^6$ It may be possible to increase III-V based MOSFET drive current at low source-drain voltages by passivating the metallic In-Ga bonds and the strained As bonds which are present in the α2-(2×4) unit cells or by using a different crystallographic face, such as the (110) surface.

III-V (110) surfaces are an appealing alternative to traditional (001) surfaces due to their lack of group V dimers and intrinsic surface defects. III-V (110) surfaces are devoid of metallic In-Ga bonds. Instead, the surface has III-V heterobonds (i.e., no homodimers), and the surface group III-V atoms are relaxed, i.e., buckled, leaving the As atoms with filled dangling bonds in a near-tetrahedral sp$^3$ geometry and the group III atoms with empty dangling bonds in a near-planar sp$^2$ geometry. The relaxed bonding structure results in the dangling bonds having electronic states outside of the bandgap$^7$ and the Fermi level of the clean surface being unpinned.

The implementation of tri-gate transistors into commercial logic chips$^8$ also increases the importance of III-V (110) surface passivation. The main benefits of using a fin based architecture are the reduction of short channel effects, minimized subthreshold swing, and a higher transconductance due to better electrostatic confinement.$^9$ The (110) surface would be the dominant surface of vertically aligned III-V (001) based finFETs$^{10}$, and with proper passivation this surface may lead to an ideal interface with the gate oxide.

In this study, the deposition of trimethylaluminum (TMA) was investigated as the Al$_2$O$_3$ seed layer on the GaAs (110) surface. While future finFETs will likely be fabricated with an InGaAs channel, GaAs was used as a model to simplify defect-free sample preparation, data interpretation, and density functional theory (DFT) modeling. Furthermore, GaAs has a wider bandgap than InGaAs so passivation techniques developed on GaAs are likely to also be effective on InGaAs. The effects of varying the dosing and the post deposition annealing (PDA) conditions upon the formation of a highly ordered monolayer with a high nucleation density were
studied since nucleation of the gate oxide atomic layer deposition (ALD) in each unit cell is critical for a minimal equivalent oxide thickness (EOT). This is the first study which uses scanning tunneling microscopy/spectroscopy (STM/STS) to study the atomic bonding configuration and electronic structure of any ALD precursor on a semiconductor (110) surface. Since the TMA reaction on GaAs (110) results in formation of Al-Ga metallic bonds, dual passivation was investigated in which the TMA/GaAs (110) surface was dosed with H$_2$O or O$_2$. DFT calculations were performed to model the bonding configuration and density of states of the clean and TMA/oxidant deposited GaAs (110) surfaces.

II. EXPERIMENTAL

The samples were either n-type GaAs (001) wafers doped with $4 \times 10^{18}$ cm$^{-3}$ Si or InGaAs (110) with a dopant level of $1 \times 10^{18}$ cm$^{-3}$ Si on InP (110). The GaAs (001) wafers were loaded into the Omicron variable temperature UHV chamber with a base pressure of $<1 \times 10^{-10}$ torr in a custom built cross-sectional sample holder. Samples were cleaved in situ to expose the (110) crystallographic face and were transferred to the scanning probe microscopy (SPM) chamber, base pressure $2 \times 10^{-11}$ torr, where STM and STS were performed. STM was used in constant current mode to determine the atomic configuration of the surface while STS was used in variable-$z$ mode to measure the electrical quality of the surface.$^{2,11,12}$ The tunneling current set point was 0.1 nA, and the samples were biased at $-2.5$ V. The STS curves were taken while ramping the sample bias from $-2.5$ V to 2.5 V and simultaneously moving the tip toward then away from the surface. All STS curves shown are an average of eight individual curves. All adsorbate structures were reproduced and the bonding configuration observed via STM and electronic structure observed via STS at least twice.

STM/STS were performed on the clean GaAs (110) surface, subsequently 10-500 Langmuirs (L) of TMA were dosed at temperatures between 25$^\circ$C and 200$^\circ$C. The samples were annealed between 135$^\circ$C and 350$^\circ$C for 30 min. All samples were annealed in an ultra-high vacuum. STM was used to probe the atomic bonding structures of partial coverage and full coverage TMA surfaces. STS was used to determine Fermi level pinning of the TMA dosed surfaces. For the dual passivation studies on GaAs (110), following TMA deposition, between 1000 and 60 000 L of H$_2$O or O$_2$ were dosed at room temperature. A series of subsequent anneals were performed in 30 min increments at 250$^\circ$C. STM and STS were performed to observe the bonding configuration and electrical characteristics of the surface after both the TMA and the oxidant were dosed. The amounts of TMA and oxidant dosed in these experiments are generally smaller than typical ALD doses by about an order of magnitude. Auger electron spectroscopy or x-ray photoelectron spectroscopy studies were not performed on GaAs(110) since the electron/x-ray beam spot size for either instrument is larger than the exposed (110) surface.

MBE grown InGaAs (110) wafers with a dopant level of $1 \times 10^{18}$ cm$^{-3}$ Si on InP (110) substrate were used to determine the presence of Al on the surface with XPS. 50 L of TMA was initially dosed at 200$^\circ$C followed by a PDA at 230$^\circ$C for 30 min. Using a home-built pulsed valve system, 5 cycles of TMA/H$_2$O were subsequently deposited. The ALD consisted of 3 s stabilization step for TMA, followed by a 10 s TMA pulse/pump step in which the sample was exposed to the entire dose volume. The H$_2$O step was identical to the TMA step but with a 5 s stabilization step. The pulse lengths in this system were long due to the low vapor pressure of the precursors and the walls of the system being at 25$^\circ$C. Five additional ALD cycles were used for STS measurements of the bandgap of the a-Al$_2$O$_3$.

An in situ monochromatic XPS (XM 1000 MkII/SPERA, Omicron Nanotechnology) was used to determine the presence of Al and O on the InGaAs (110) surface. The XPS was operated in constant analyzer energy mode with a pass energy of 50 eV and the line width of 0.1 eV using an Al K$_\alpha$ source (1486.7 eV). The takeoff angle was 30$^\circ$ relative the surface with an acceptance angle of 7$^\circ$. CASA XPS v.2.3 was used to analyze the data. The relative intensities of the core-level peaks were quantified by calculating the peak area and dividing by the relative sensitivity factors.

All DFT simulations were performed with the Vienna Ab-Initio Simulation Package (VASP)$^{13,14}$ using projector augmented-wave (PAW) pseudopotentials (PP)$^{15}$ and the PBE (Perdew-Burke-Ernzerhof) exchange-correlation functional.$^{16,17}$ The choices of PBE functional and PAW PP were validated by parameterization runs demonstrating good reproducibility of experimental lattice constants, bulk moduli, and formation/cohesive energies for bulk crystalline GaAs.

III. RESULTS AND DISCUSSION

A. STM of TMA deposition on GaAs (110) surface

The cleaved GaAs (110) surface has been well studied with STM.$^{18-21}$ STM was initially employed in this study to ensure the surface was free of contaminants and defects; Fig. 1(a) shows a filled state 10 $\times$ 10 nm$^2$ STM image of the clean GaAs (110) surface. The crystallographic directions are slightly tilted due to drift in the piezo in the scanner; this is an inherent problem which is observed in several of the images. The rows oriented in the (110) direction are comprised of a zigzag chain of Ga and As atoms with heterobonds; this chain is depicted in a model of the clean surface shown in Fig. 1(b).

The GaAs (110) zigzag chain is buckled so that each surface As atom is elevated relative to each surface Ga atom$^{22,23}$ because the filled dangling bonds on the As atoms induce near tetrahedral (sp$^3$) bonding angles, while the empty dangling bonds on the Ga atoms allow near planar (sp$^3$) bonding angles. The filled dangling bonds on the As atoms are directly observed in filled state STM images.

Initially, 5 L of TMA was dosed at 25$^\circ$C followed by an anneal at 135$^\circ$C for 30 min to obtain partial coverage. As shown in Fig. 2, STM reveals regions of the clean surface (red circle) as well as regions that have reacted with TMA (blue box). The blue box contains two sites where it is hypothesized that two TMA molecules have dissociatively chemisorbed as dimethylaluminum (DMA) between the clean
FIG. 1. Clean GaAs (110). (a) A filled state STM image of the clean GaAs (110) surface. The filled dangling As bonds are directly observed resulting in rows oriented in the (\bar{1}10) direction. (b) A model of the clean GaAs (110) surface showing the filled As dangling bonds (filled ovals) and empty Ga dangling bonds (empty ovals). Notice the As-Ga rows are buckled which allows each As atom to be in a nearly sp^3 geometry and each Ga to be in a nearly sp^2 geometry.

GaAs rows. Line traces indicate these reacted sites are 0.5 Å above the clean surface. A reaction between TMA and the surface has occurred, but a larger dose is necessary to achieve full coverage.

Exposure of the clean surface to 10 L of TMA at 25 °C and a subsequent anneal at 135 °C for 30 min resulted in the formation of \sim 1/3 of a monolayer (ML) of adsorbates. Ordered rows of chemisorbates formed which are rotated 40° clockwise relative to the clean surface rows, as shown in Fig. 3. The line trace in the inset in Fig. 3 shows the spacing between adjacent rows was 17 Å, 3 \times the spacing of the clean surface rows. A proposed qualitative model for low coverage TMA chemisorption is shown in Fig. 3(b). Three DMA molecules reacted with the surface in a stepwise manner, giving the appearance of diagonal rows. DFT was not used to quantitatively model this system due to the size of the unit cell. For full passivation, it is necessary to increase this nucleation density while maintaining surface order.

Exposure of the clean surface to 50 L of TMA at 200 °C followed by an anneal at 230 °C for 30 min resulted in formation of an ordered monolayer of DMA with some defect sites. Figure 4(a) shows the ordered rows are oriented in the (\bar{1}10) direction. The spacing between adjacent rows was measured to be 5.6 Å (see insert) which is identical to the spacing of the clean surface rows indicating the maximum nucleation density has been achieved. A model for the full coverage chemisorption of TMA is shown in Fig. 4(b). It is proposed that TMA loses a methyl group, and the resulting dimethylaluminum (DMA) makes one Al-As bond and one Al-Ga bond. This is the likely bonding geometry since bonding between adjacent As or Ga row atoms is not possible without each atom making five total bonds, which is likely energetically unfavorable. The full coverage DMA surface has three different reacted sites. The pink circle in Fig. 4(a) shows a dim site where DMA has bonded in the ideal configuration with rows oriented in the (\bar{1}10) direction; this is the predominant chemisorption site and is modeled below with DFT to confirm the assignment. The yellow boxes show dim diagonal sites. The rows at these sites appear rotated 40° relative to the (\bar{1}10) direction. These diagonal sites are believed to be DMA bonded between adjacent clean surface rows in a stepwise fashion giving the appearance of a diagonal row, similar to the low coverage case. The diagonal sites are never observed on the clean GaAs (110) surface. The diagonal sites are the same height as the vertical rows consistent with having nearly a full monolayer of DMA. It is noted that diagonal sites are not observed after large TMA doses (500 L). The blue triangle indicates a bright site on the full coverage...
FIG. 3. Medium coverage TMA/GaAs (110). (a) STM image after 10 L dose of TMA at 25 °C followed by an anneal at 135 °C for 30 min. Rows are observed rotated 40° clockwise relative to the clean surface rows. Spacing between adjacent rows is 17 Å as shown in the line trace. (b) Proposed model for low coverage TMA chemisorption on GaAs (110). TMA dissociatively chemisorbs as DMA in a stepwise fashion giving the appearance in STM of a row (orange rectangle) that is rotated 40° clockwise relative to the clean surface rows.

surface. These are hypothesized to be AlO_x sites that form when background water in the dosing chamber reacts with the freshly deposited DMA monolayer. H_2O was not intentionally introduced into the system during this experiment. It is believed that water dissociatively chemisorbs between adjacent Al atoms and a TMA molecule subsequently chemisorbs onto the bridge bonding O atom. The height of these bright sites is 2 Å and two models have been proposed to explain these features (see below).

An annealing study was performed to determine the characteristics of DMA chemisorption on the clean GaAs (110) surface. After 500 L of TMA was dosed at 250 °C and subsequently annealed to 260 °C for 30 min, two different ordered regions appear, shown in Fig. 5(a). The blue arrow indicates regions of highly ordered rows with 5.6 Å spacing between adjacent rows, similar to the ideal bonding configuration in Fig. 4(a). The red arrow in Fig. 5(a) indicates regions with 11 Å spacing between adjacent rows, 2x the spacing of the clean surface which is not observed in the ideal TMA terminated surface shown in Fig. 4(a). The hemispherical bright sites (green circle), believed to be AlO_x, initially average 2.5 Å in diameter. The same sample was subsequently annealed to 300 °C for an additional 60 min, shown in Fig. 5(b). The red box highlights regions of clean GaAs (110) that have been exposed by annealing; additionally, the AlO_x clusters have grown wider and taller with an average diameter of 3.5 Å. This suggests after annealing to 300 °C the bright sites (green circle) coalesce and this results in regions of TMA-free clean GaAs (110). There are also dim reacted sites (yellow triangle) that remain on the surface which are likely DMA or MMA molecules that have not desorbed. A small amount of vertical ordering remains, but the nucleation density has dramatically decreased. A final anneal to 350 °C for 60 min was performed, Fig. 5(c), and the AlO_x clusters grew to an average diameter of 6 Å and larger regions of the clean surface became exposed, as seen in the red box in Fig. 5(c). A few dim sites remain indicating sites where DMA molecules have remained in their initial chemisorption sites, but no vertical ordering is evident. There is a large thermodynamic driving force to form Al-O bonds (511 kJ/mol), and when the sample is heated, the O atoms diffuse on the surface and form highly stable clusters of AlO_x. This set of experiments demonstrates that the TMA bonding is relatively weak and does not perturb the bonds
FIG. 5. Effect of anneal temperature after high TMA dose on GaAs(110). (a) STM image of 500 L TMA dose at 250°C with subsequent anneal at 260°C for 30 min. The blue arrow indicates regions with 5.6 Å spacing between adjacent rows which is observed for the full coverage surface. The red arrow indicates regions with 11 Å spacing between adjacent rows corresponding to a decreased nucleation density. There are bright sites (green circle) which are believed to be AlOx and initially average 2.5 Å in diameter. (b) STM image of the same sample annealed to 300°C for 60 min. Areas of clean surface (red box) are visible as well as formation of large white adsorbate clusters (green circle). It is hypothesized that AlOx clusters are coalescing which results in the larger bright sites and a larger area of exposed clean surface. (c) Same sample annealed to 350°C for 60 min. Larger areas of clean surface are visible (red box) and bright clusters continue to coalesce (green circle) with average diameters of 6 Å. DMA molecules which have remained in their initial chemisorption sites (yellow triangle) are also visible.

within the substrate, but any oxygen present on the surface will react with Al and cluster at temperatures above 200°C.

Figure 6 shows a STM image obtained after dosing the full coverage DMA/GaAs (110) surface with 1000 L of O2 at 25°C followed by an anneal at 230°C for 30 min and a subsequent anneal at 250°C for 60 min. Ordered rows are visible in the (110) direction (blue lines) indicating that after oxidant dosing the surface order is maintained. The dark sites (green box) are hypothesized to be sites in which a DMA molecule has been scavenged by oxygen resulting in exposure of the clean surface while the bright sites (red arrow) are believed to be sites that have reacted with more than one –O– atom resulting in a site that is protruding from the surface, hence appearing bright in STM.

FIG. 6. STM of O2/TMA/GaAs (110). Filled state STM image of theDMA/GaAs (110) surface dosed with 1000 L of O2 at 25°C followed by an anneal at 230°C for 30 min and subsequently 250°C for 1 h. Ordered rows are visible (blue lines) in the (110) direction indicating the surface order is maintained after dosing O2. The dark sites (green square) are hypothesized to be sites in which oxygen has scavenged a DMA molecule exposing the clean surface while the bright sites (red arrow) are hypothesized to be sites that have reacted with more than one O atom resulting in a site protruding from the surface.

B. STS of TMA deposition on GaAs (110) surface

STS probes the local density of states (LDOS) of the surface. Experiments were only performed with n-type GaAs (110) since Fermi level pinning results in a Fermi level position slightly below midgap independent of n vs. p doping thereby making only measurement on n-type samples fully diagnostic.

Figure 7 compares the STS spectra of the clean GaAs (110) surface and full coverage DMA surface. The clean surface (black curve) Fermi Level (Ef), which is defined as the 0 V position, is located about 0.4 V from the CB indicating an unpinned Ef. The full coverage DMA surface (blue curve) shows the Ef has shifted to midgap, indicative of surface pinning.

FIG. 7. STS spectra of the clean surface (black) and full coverage TMA surface (blue). The Ef for the clean surface is located near the CB indicating an unpinned surface. The full coverage surface has a large CB edge state starting at 0.5 V and the Ef has shifted to midgap indicating the surface is pinned.
pinning. Additionally, a large CB edge state is observed starting at ~0.5 V. This data indicates that a highly ordered monolayer of DMA on the (110) surface pins the Fermi level near midgap consistent with DFT calculations which suggest the CB edge state is a result of Al-Ga bond formation.

STS was performed on the oxidant dosed DMA/GaAs surface. Figure 8 compares the full coverage TMA surface (blue curve) with O2 or H2O dosed surfaces. The CB edge state is dramatically reduced after dosing the DMA surface with 1000 L of O2 at 25°C followed by an anneal at 250°C for 30 min (red curve) consistent with the hypothesis that O inserts into the Al-Ga metallic bonds. A small CB edge states remains, indicating not all of the metallic bonds have been passivated. A subsequent 59 000 L dose of O2 at 25°C with an anneal at 250°C for 30 min (olive curve) did not remove the remaining CB edge states, but it slightly shifted the Ef toward the CB consistent with further passivation. In a separate experiment, 2000 L of H2O was dosed onto the DMA/GaAs (110) surface at 25°C followed by an anneal at 250°C for 30 min (red curve) consistent with the hypothesis that O has inserted into the Al-Ga metallic bonds. A small CB edge states remains, indicating not all of the metallic bonds have been passivated. A subsequent 59 000 L dose of O2 at 25°C with an anneal at 250°C for 30 min (olive curve) did not remove the remaining CB edge states, but it slightly shifted the Ef toward the CB consistent with further passivation. In a separate experiment, 2000 L of H2O was dosed onto the DMA/GaAs (110) surface at 25°C followed by an anneal at 250°C for 30 min (black curve), and the CB edge states were completely passivated. It is hypothesized that the water dissociates and the –OH groups preferentially insert between the Al-Ga metallic bonds, similar to the –O–insertion, consistent with the DFT calculations below.

Since it was not possible to confirm the presence of aluminum on the cleaved GaAs (110) surface, MBE grown InGaAs (110) samples were employed to confirm a complete monolayer of DMA chemisorbs to the surface. STS was performed of the InGaAs (110) TMA/H2O dosed surface to ensure correlation with the TMA/H2O dosed GaAs (110) results. Figure 9 compares three STS curves. The clean InGaAs (110) surface (blue) has a bandgap of about 0.8 eV. After dosing 50 L of TMA at 200°C followed by an anneal at 230°C for 30 min and 5 subsequent cycles of Al2O3 ALD (green curve) the bandgap increased to 2 eV. About 30 STS spectra were taken at three different locations on the sample to ensure sample uniformity across a range of surface sites. After 10 cycles of Al2O3 ALD the band gap increases to 2.94 ± 0.25 eV. The bandgap increasing to that of a thin amorphous film of Al2O3 after 10 cycles is consistent with having an ordered monolayer of DMA with a high nucleation density on the InGaAs (110) surface which serves as the template for ALD of Al2O3.

XPS was performed on the sample which had 10 ALD cycles, and it was found that the ratio of Al to O was 0.65, consistent with experimental data showing the clean surface has an unpinned Fermi level. The full coverage DMA model (b) shows each Al atom bonding to an As atom and a Ga atom. The DOS shows a large conduction band (CB) edge state which is attributed to the chemisorption of TMA resulting in a metallic Al-Ga bond (red arrow). This supports the proposed model in Fig. 3 for DMA chemisorption in which each Al atom will make an Al-As bond and an Al-Ga bond. Experimentally, the CB edge state is observed consistent with the presence of the metal-metal bonds pinning the Ef midgap. The DFT calculated DOS shows that by inserting an –OH– group (c) into the metallic Al-Ga bond the CB edge state is fully passivated. This insertion eliminates any metallic bond.
character and restores the DOS to that of the clean surface. In (d), oxygen was inserted and –O– atoms bonded between the metallic Al-Ga bond and the CB edge states were suppressed. This is a result of oxidizing the metallic bond and should result in an unpinned surface $E_F$. In (d), one of the methyl groups from DMA has bonded to the O atom, but the DOS shows this does not have a significant effect on the electronic structure.

Figure 11 shows two different models for the bright sites observed in Fig. 4(a). It is proposed that in each model DMA forms a monolayer as discussed above, after formation of the initial monolayer a background $H_2O$ or $O_2$ molecule dissociatively chemisorbs between (a) two DMA molecules along the GaAs (110) row direction or (b) between DMA molecules that are bonded to adjacent GaAs (110) rows. Subsequently, an additional DMA molecule from TMA was placed onto the bridging O atom since the experiments were performed with excess TMA. Note the models in Fig. 10 show two adjacent defect sites. The bright sites in Fig. 4(a) are believed to consist of only one defect site, but the double defect sites were modeled to be sure the defects do not cross react. These models result in defect sites which are about 2 Å taller than the DMA only sites. The height difference is what causes the defects to appear bright in the STM image in Fig. 4(a). Model (a) shows a TMA molecule as a volatile reaction product consistent with TMA having weak bonding to the bridging O atoms in part due to steric hindrance. In contrast, model (b) has $C_2H_4$ and $H_2$ as volatile reaction products consistent with DMA having ligands which readily desorb. The total energy for each system was calculated and model (a) had a total energy of $-2.59$ eV lower (i.e., more stable) than model (b). Since model (a) is the most thermodynamically favorable structure and it is expected that this site would appear bright in Fig. 4(a) because they are about 2 Å taller than a DMA only site, this is assigned as the structure for the bright defects in Fig. 4(a).
IV. CONCLUSION

A defect-free GaAs (110) surface has been employed to nucleate the ALD of Al2O3 in every unit cell while maintaining a highly ordered smooth surface. Passivation of III-V (110) surfaces is especially challenging since the surfaces are dominated by heterobonds so a precursor will make bonds to both the group III and group V atoms potentially pinning the Fermi level. It was proposed that TMA dissociatively chemisorbs to the surface, making one Al-As bond and one Al-Ga bond. DFT was used to model this system and the calculated DOS show a large CB edge state which was caused by chemisorption of TMA on the surface resulting in formation of a metal-metal bond. To passivate this CB state –OH and –O– groups were inserted into the metallic bonds on the surface; in the DFT model this completely suppressed the CB edge state. Experimental work verified the theoretical work and it was shown that by starting with a clean GaAs (110) surface, it is possible to form an ordered monolayer of TMA. STS was used to verify that the TMA monolayer has a large CB edge state. By utilizing a dual passivation scheme where the TMA surface was dosed with either O2 or H2O this state was suppressed due to elimination of the metal-metal bonds.

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24See supplementary material at http://dx.doi.org/10.1063/1.4852155 for model of surface As/Ga making 5 bonds and XPS data.